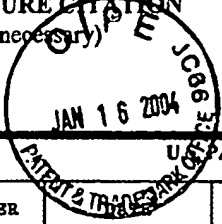



INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				Docket Number (Optional) YOR920030541US1 (17113)		Application Number 10/696,632	
				Applicant(s) Harold J. Hovel, et al.			
				Filing Date October 29, 2003		Group Art Unit Unassigned	



UNITED STATES PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TSP		6,429,145 B1	8/6/02	Hovel			

FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
TSP	"Temperature And Magnetic Field Dependence Of The Carrier Mobility In SOI-Wafers By The Pseudo-MOSFET Method," Electrochemical Society Proceedings, by C. Rossel, et al., pp. 479-486
TSP	"Si Film Electrical Characterization in SOI Substrates by the HgFET Technique," Solid State Electronics, by H.J. Hovel pp. 1311-1333, 2003
TSP	"Extremely Low Resistivity Erbium Ohmic Contacts To n-type Silicon," Physics Letters, by P.L. Janega, et al., pp. 1415-1417
TSP	"The Schottky-barrier Height Of The Contacts Between Some Rare-earth Metals (and silicides) And p-type Silicon," 1981 American Institute of Physics, by H. Norde, et al., pp. 865-867

EXAMINER 	DATE CONSIDERED 5/23/05
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.